

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

4N35(Short), 4N36(Short), 4N37(Short)

AC LINE /DIGITAL LOGIC ISOLATOR.

DIGITAL LOGIC /DIGITAL LOGIC ISOLATOR.

TELEPHONE LINE RECEIVER.

TWISTED PAIR LINE RECEIVER.

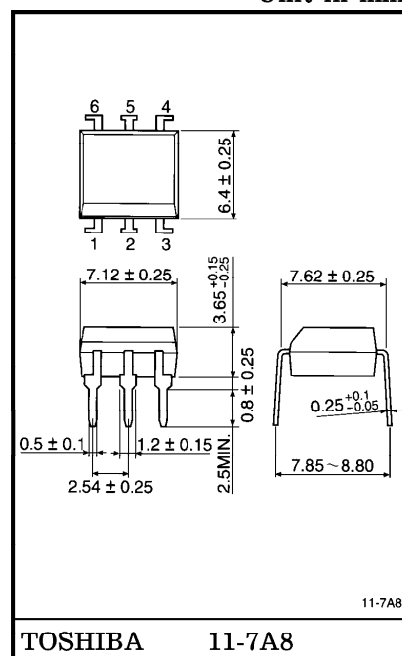
HIGH FREQUENCY POWER SUPPLY FEEDBACK CONTROL.

RELAY CONTACT MONITOR.

The TOSHIBA 4N35 (Short) through 4N37 (Short) consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor in a dual in-line package.

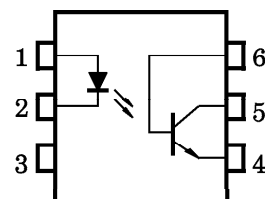
- Switching Speeds : $3\mu\text{s}$ (Typ.)
- DC Current Transfer Ratio : 100% (Min.)
- Isolation Resistance : $10^{11}\Omega$ (Min.)
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

Unit in mm



Weight : 0.4g

PIN CONFIGURATIONS (Top view)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : EMITTER
- 5 : COLLECTOR
- 6 : BASE

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- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT
LED	Forward Current (Continuous)		I_F	60	mA
	Forward Current Derating		$\Delta I_F / ^\circ\text{C}$	0.8 (*)	mA / °C
	Peak Forward Current (Note 1)		I_{PF}	3	A
	Power Dissipation		P_D	100	mW
	Power Dissipation Derating		$\Delta P_D / ^\circ\text{C}$	1.33 (*)	mW / °C
	Reverse Voltage		V_R	6	V
DETECTOR	Collector-Emitter Voltage		BV_{CEO}	30	V
	Collector-Base Voltage		BV_{CBO}	70	V
	Emitter-Collector Voltage		BV_{ECO}	7	V
	Collector Current (Continuous)		I_C	100	mA
	Power Dissipation		P_C	300	mW
	Power Dissipation Derating		$\Delta P_C / ^\circ\text{C}$	4.0 (*)	mW / °C
COUPLED	Storage Temperature		T_{stg}	-55~150	°C
	Operating Temperature		T_{opr}	-55~100	°C
	Lead Soldering Temperature (at 10s)		T_{sol}	260	°C
	Total Package Power Dissipation		P_T	300	mW
	Total Package Power Dissipation Derating		$\Delta P_T / ^\circ\text{C}$	3.3 (*)	mW / °C
			BV_S	2500	Vrms
	Input to Output Isolation Voltage (AC, 1 Minute)	4N35	$BV_S (**)$	2500 / 3550	Vrms / Vpk
		4N36		1750 / 2500	
		4N37		1050 / 1500	

(Note 1) Pulse width 1 μ s, 300pps

(*) Above 25°C ambient.

(**) JEDEC registered maximum BV_S , however, TOSHIBA specifies a maximum BV_S of 2500V_{rms}, 1 minute.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	0.8	1.15	1.5	V
			$I_F = 10\text{mA}$, Ta = -55°C	0.9	—	1.7	
			$I_F = 10\text{mA}$, Ta = 100°C	0.7	—	1.4	
	Reverse Current	I_R	$V_R = 6\text{V}$	—	—	10	μA
	Capacitance	C_D	V = 0, f = 1MHz	—	30	100	pF
DETECTOR	DC Forward Current Gain	h_{FE}	$V_{CE} = 5\text{V}$, $I_C = 500\mu\text{A}$	—	200	—	—
	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}$	30	—	—	V
	Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$	70	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 100\mu\text{A}$	7	—	—	V
	Collector Dark Current	I_{CEO}	$V_{CE} = 10\text{V}$	—	1	50	nA
	Collector Dark Current	I_{CEO}	$V_{CE} = 30\text{V}$, Ta = 100°C	—	—	500	μA
	Collector-Emitter Capacitance	C_{CE}	V = 0, f = 1MHz	—	10	—	pF
COUPLED	Current Transfer Ratio		$I_F = 10\text{mA}$, $V_{CE} = 10\text{V}$	100	—	—	%
			$I_F = 10\text{mA}$, $V_{CE} = 10\text{V}$ Ta = -55°C	40	—	—	
			$I_F = 10\text{mA}$, $V_{CE} = 10\text{V}$ Ta = 100°C	40	—	—	
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F = 10\text{mA}$, $I_C = 0.5\text{mA}$	—	0.1	0.3	V
	Capacitance Input to Output	C_S	$V_S = 0$, f = 1MHz	—	0.8	2.5	pF
	Isolation Resistance	R_S	$V_S = 500\text{V}$, R. H. $\leq 60\%$	10^{11}	—	—	Ω
	Input to Output Isolation Current (Pulse Width = 8ms)	I_{IO}	$V_{iO} = 3550\text{Vpk}$	—	—	100	μA
			$V_{iO} = 2500\text{Vpk}$	—	—	100	
			$V_{iO} = 1500\text{Vpk}$	—	—	100	
	Turn-On Time	t_{ON}	$V_{CC} = 10\text{V}$, $I_C = 2\text{mA}$	—	3	10	μs
	Turn-Off Time	t_{OFF}	$R_L = 100\Omega$	—	3	10	

